

FAST MRI PROTECTION DIODES

RoHS Compliant Versions Available

DESCRIPTION

The UM9989 diode series was designed to protect MRI receivers from high RF energy fields including long RF pulses and RF spike pulses present in most MRI machines. The UM9989 acts as a passive protector (limiter) for the MRI receiver. No forward bias voltage is required to turn on the diode. It is self-biased by the RF transmitter pulse power. A switch driver is not needed for this receiver protection application.

Receiver protector diodes appear directly across the input port of the receiver. They are connected in anti-parallel pairs to limit the RF carrier excursion in both polarities. They must, therefore, exhibit extremely low insertion loss, both in the "on" state (high power present) and the "off" state (receiver power present) so as not to decrease the receiver's sensitivity. The UM9989 diodes are available in two package configurations for flexibility in design.

IMPORTANT: For the most current data, visit our website: www.MICROSEMI.com

ABSOLUTE MAXIMUM RATINGS AT 25°C (UNLESS OTHERWISE SPECIFIED) Rating Symbol Value Unit Peak Repetitive Reverse Voltage V_{RRM} Working Peak Reverse Voltage 75 V V_{RWM} DC Blocking Voltage V_R RMS Reverse Voltage V_{R (RMS)} V 50 Non-Repetitive Peak Forward Surge Current I_{FSM} 2.5 Α 8.3ms Single half sine wave ٥С Storage Temperature T_{STG} -65 to +150 ٥С Operating Temperature T_{OP} -65 to +150





Style "B"

Style "SM"

KEY FEATURES

- Available in surface mount package.
- Metallurgical bond
- Planar passivated chip
- Ultra Low magnetic construction
- Non cavity design
- Thermally matched configuration
- Low capacitance at 0 V bias
- Low conductance at 0 V bias
- Compatible with automatic insertion equipment
- RoHS Compliant Versions Available¹

APPLICATIONS/BENEFITS

- MRI receiver protection
- Body coil isolation

Note 1: RoHS compliant versions are supplied with a matte Tin finish. RoHS part numbers are: UMX9989B UMX9989SM



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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
	T				T	
Forward Voltage (Note 1)	V_{F}	$I_F = 10 \text{ mA}$, $T_J = 25 ^{\circ}\text{C}$			1.0	٧
	V F	$I_F = 100 \text{ mA}$, $T_J = 25 ^{\circ}\text{C}$			1.2	V
Reverse Break Down Voltage (Note 1)	V_{BR}	I _R = 100 uA	75			V
Reverse Current (Note1)	I _R	$V_R = 20 \text{ V}, \ T_J = 25 ^{\circ}\text{C}$			50	nA
		V _R = 50 V, T _J = 25 °C			500	nA
Capacitance	Ст	V _R = 0V, F = 1 MH _Z		1.2	5	pF
Conductance	G	V _R = 0 V, F = 64 MHz			40	uS

Note: 1 Short duration test pulse used to minimize self heating effect.

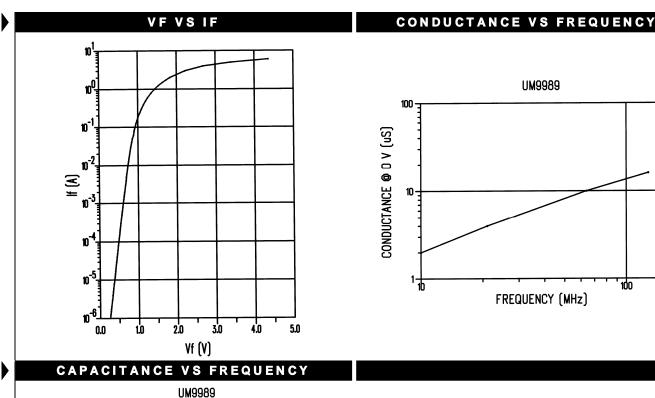
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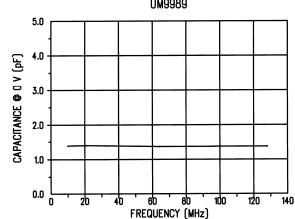
150



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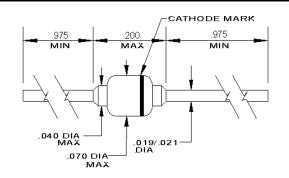




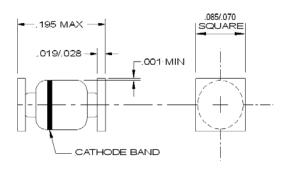
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UM9989B



UM9989SM



SM STYLE SOLDER FOOTPRINT

